

# 2SC3507

## Silicon NPN triple diffusion planar type

For high breakdown voltage high-speed switching

### ■ Features

- High-speed switching
- High collector-base voltage (Emitter open)  $V_{CBO}$
- Satisfactory linearity of forward current transfer ratio  $h_{FE}$
- Full-pack package which can be installed to the heat sink with one screw

### ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

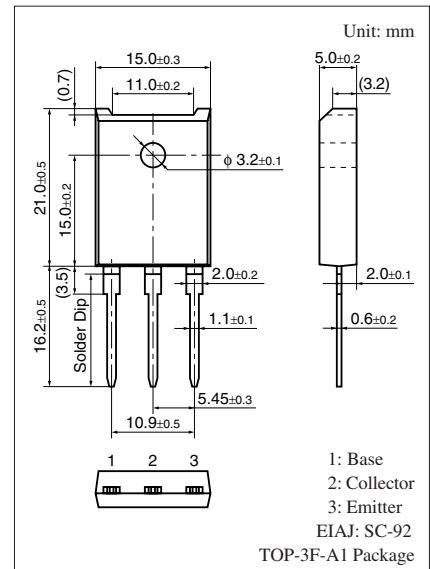
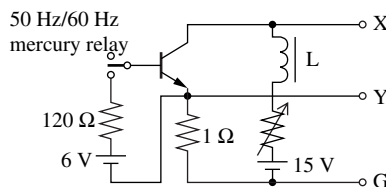
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	1 000	V
Collector-emitter voltage (E-B short)	$V_{CES}$	1 000	V
Collector-emitter voltage (Base open)	$V_{CEO}$	800	V
Emitter-base voltage (Collector open)	$V_{EBO}$	7	V
Collector current	$I_C$	5	A
Base current	$I_B$	3	A
Peak collector current	$I_{CP}$	10	A
Collector power dissipation	$P_C$	80	W
	$T_a = 25^\circ\text{C}$	3.0	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

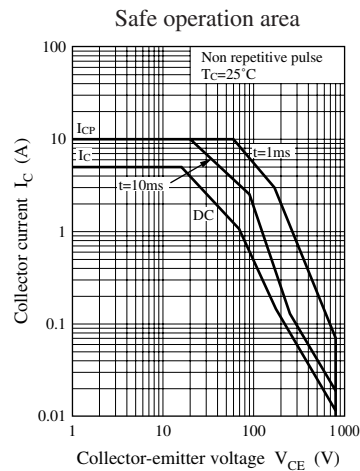
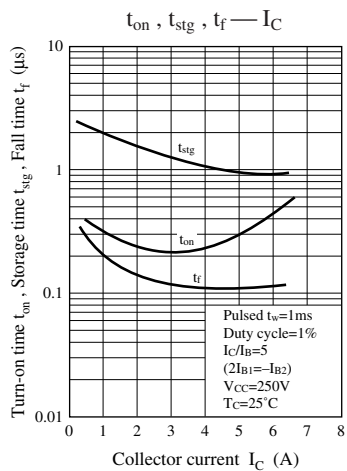
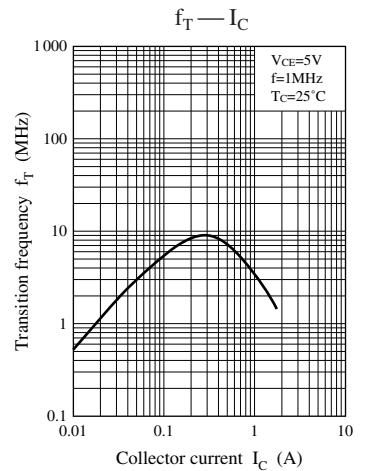
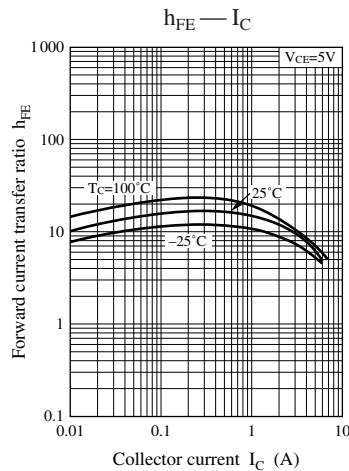
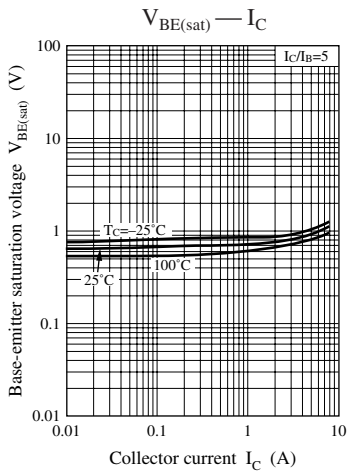
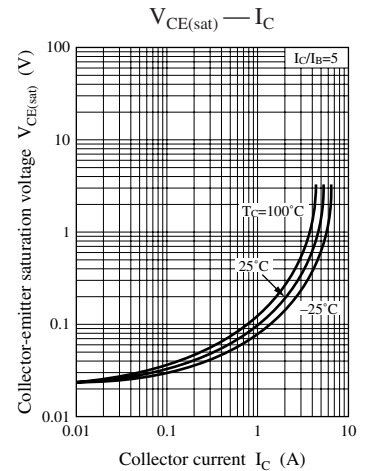
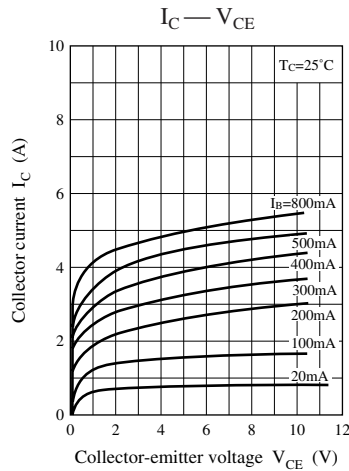
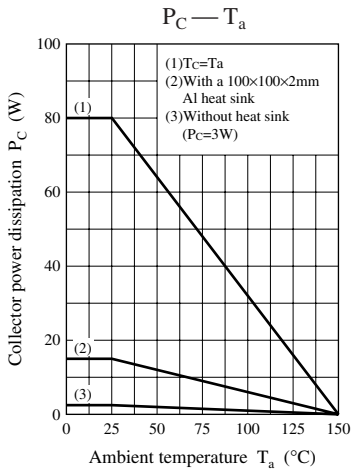
### ■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter sustaining voltage *	$V_{CEO(SUS)}$	$I_C = 0.5 \text{ A}$ , $L = 50 \text{ mH}$	800			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 1\,000 \text{ V}$ , $I_E = 0$			50	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 7 \text{ V}$ , $I_C = 0$			50	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 5 \text{ V}$ , $I_C = 3 \text{ A}$	6			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 3 \text{ A}$ , $I_B = 0.6 \text{ A}$			1.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 3 \text{ A}$ , $I_B = 0.6 \text{ A}$			1.5	V
Transition frequency	$f_T$	$V_{CE} = 5 \text{ V}$ , $I_C = 0.5 \text{ A}$ , $f = 1 \text{ MHz}$		6		MHz
Turn-on time	$t_{on}$	$I_C = 3 \text{ A}$			1.0	$\mu\text{s}$
Storage time	$t_{stg}$	$I_{B1} = 0.6 \text{ A}$ , $I_{B2} = -1.2 \text{ A}$			2.5	$\mu\text{s}$
Fall time	$t_f$	$V_{CC} = 250 \text{ V}$			0.5	$\mu\text{s}$

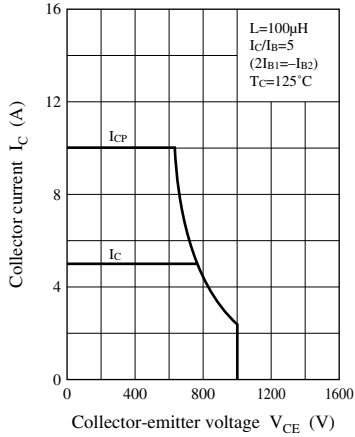
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*:  $V_{CEO(SUS)}$  test circuit

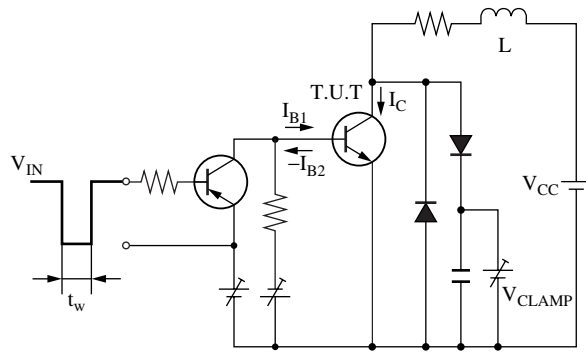




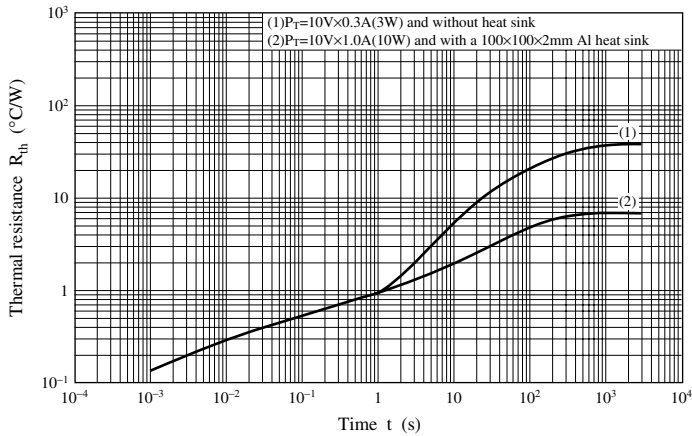
Safe operation area (Reserve bias)



Safe operation area (Reserve bias) measurement circuit



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